Magnetic and Transport Properties of Amorphous GdGe Alloys near the Metal-Insulator Transition

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It is suggested that the large effects of matrix (Ge vs Si) are due to differences in dielectric constant and bandgap, which cause changes in screening, thereby altering the effect of the magnetic moments of Gd on both localization of carriers and on the indirect mediated Gd-Gd exchange interactions. We thank the NSF for support.

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Date submitted: 16 Dec 2004  Electronic form version 1.4